

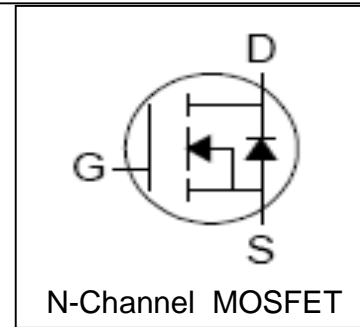
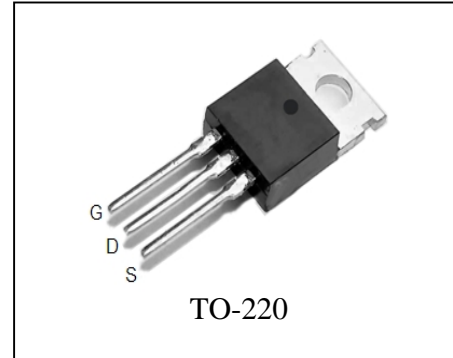
Features

- 800V/7A,
 $R_{DS(ON)} = 1.6\Omega$ (Typ.) @ $V_{GS} = 10V$
- Gate charge minimized
- Low C_{rss} (Typ. 15pF)
- Extremely high dv/dt capability
- 100% avalanche tested
- Lead Free and Green Available

Applications

- High efficiency switch mode power supplies
- Lighting

Pin Description



Absolute Maximum Ratings

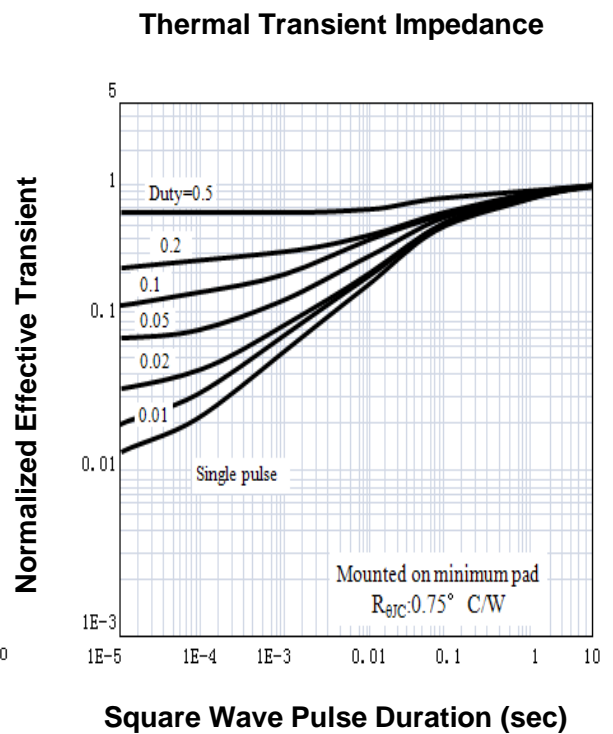
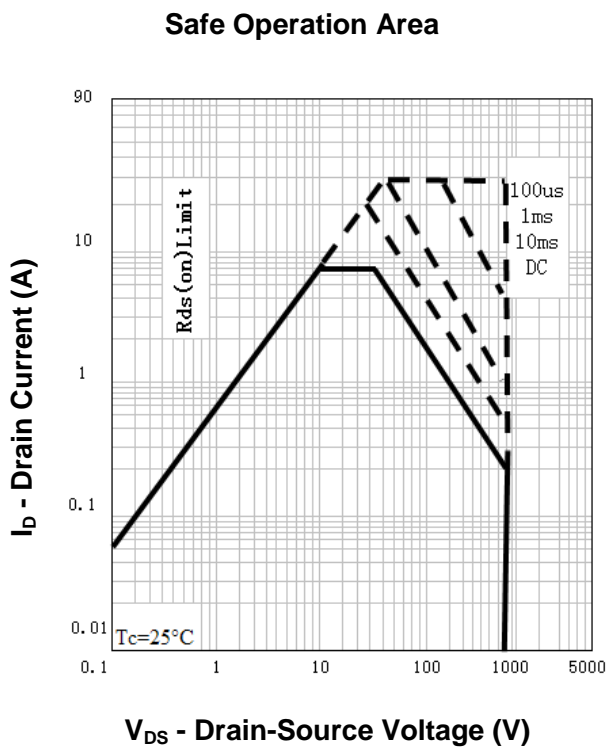
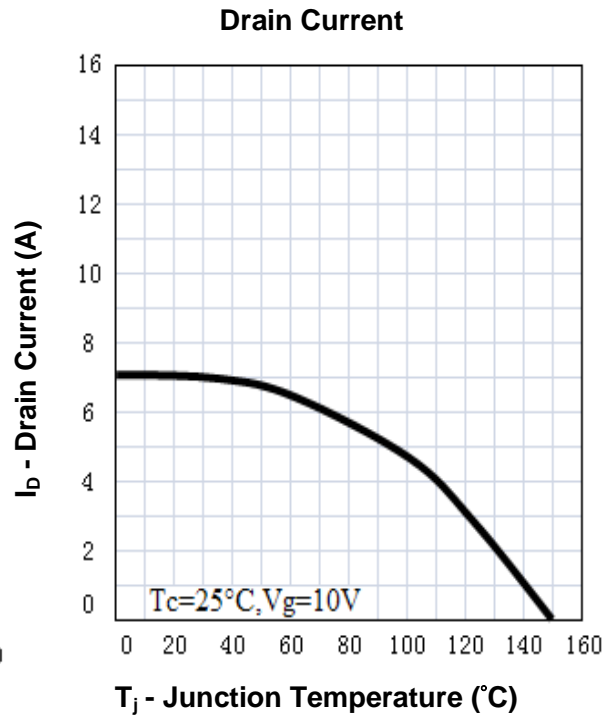
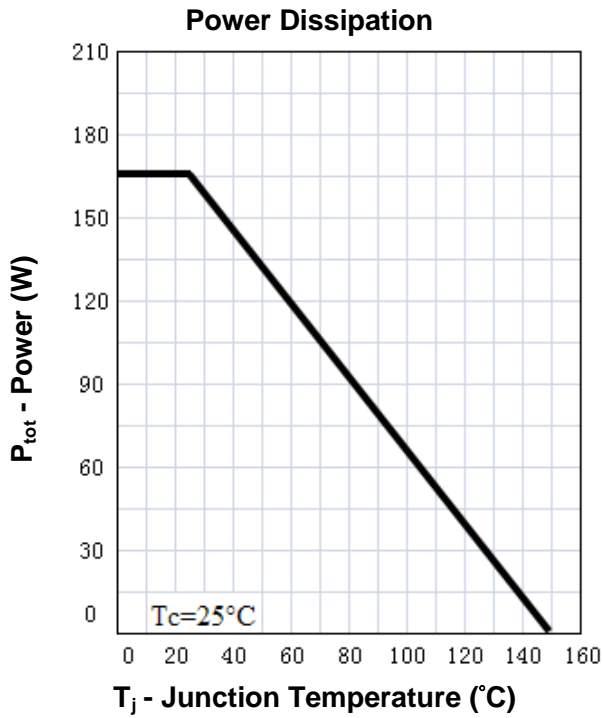
Symbol	Parameter	Rating	Unit
Common Ratings ($T_C = 25^\circ\text{C}$ Unless Otherwise Noted)			
V_{DSS}	Drain-Source Voltage	800	V
V_{GSS}	Gate-Source Voltage	± 30	
T_J	Maximum Junction Temperature	150	$^\circ\text{C}$
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
I_S	Diode Continuous Forward Current	$T_C = 25^\circ\text{C}$ 7	A
Mounted on Large Heat Sink			
I_{DP}	300 μs Pulse Drain Current Tested	$T_C = 25^\circ\text{C}$ 28 ^①	A
I_D	Continuous Drain Current ($V_{GS} = 10V$)	$T_C = 25^\circ\text{C}$ 7 ^①	A
		$T_C = 100^\circ\text{C}$ 4.5 ^①	
P_D	Maximum Power Dissipation	$T_C = 25^\circ\text{C}$ 167	W
		$T_C = 100^\circ\text{C}$ 67	
$R_{\theta JC}$	Thermal Resistance-Junction to Case	0.75	$^\circ\text{C/W}$
Drain-Source Avalanche Ratings			
E_{AS} ^②	Avalanche Energy, Single Pulsed	45	mJ

Electrical Characteristics ($T_C=25^\circ\text{C}$ Unless Otherwise Noted)

Symbol	Parameter	Test Condition	RU8H7R			Unit
			Min.	Typ.	Max.	
Static Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_{DS}=250\mu A$	800			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=800V, V_{GS}=0V$			1	μA
		$T_J=85^\circ C$			30	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_{DS}=250\mu A$	2.5	-	4.5	V
I_{GSS}	Gate Leakage Current	$V_{GS}=\pm 30V, V_{DS}=0V$			± 100	nA
$R_{DS(ON)}^{(3)}$	Drain-Source On-state Resistance	$V_{GS}=10V, I_{DS}=3.5A$		1.6	1.9	Ω
Diode Characteristics						
$V_{SD}^{(3)}$	Diode Forward Voltage	$I_{SD}=7A, V_{GS}=0V$			1.2	V
t_{rr}	Reverse Recovery Time	$I_{SD}=7A, di_{SD}/dt=100A/\mu s$		780		ns
Q_{rr}	Reverse Recovery Charge			9		μC
Dynamic Characteristics ⁽⁴⁾						
R_G	Gate Resistance	$V_{GS}=0V, V_{DS}=0V, F=1MHz$		10		Ω
C_{iss}	Input Capacitance	$V_{GS}=0V,$ $V_{DS}=400V,$ Frequency=1.0MHz		1550		pF
C_{oss}	Output Capacitance			145		
C_{rss}	Reverse Transfer Capacitance			15		
$t_{d(ON)}$	Turn-on Delay Time	$V_{DD}=400V, R_L=57\Omega,$ $I_{DS}=7A, V_{GEN}=10V,$ $R_G=25\Omega$		40		ns
t_r	Turn-on Rise Time			120		
$t_{d(OFF)}$	Turn-off Delay Time			60		
t_f	Turn-off Fall Time			70		
Gate Charge Characteristics ⁽⁴⁾						
Q_g	Total Gate Charge	$V_{DS}=640V, V_{GS}=10V,$ $I_{DS}=7A$		35		nC
Q_{gs}	Gate-Source Charge			10		
Q_{gd}	Gate-Drain Charge			13		

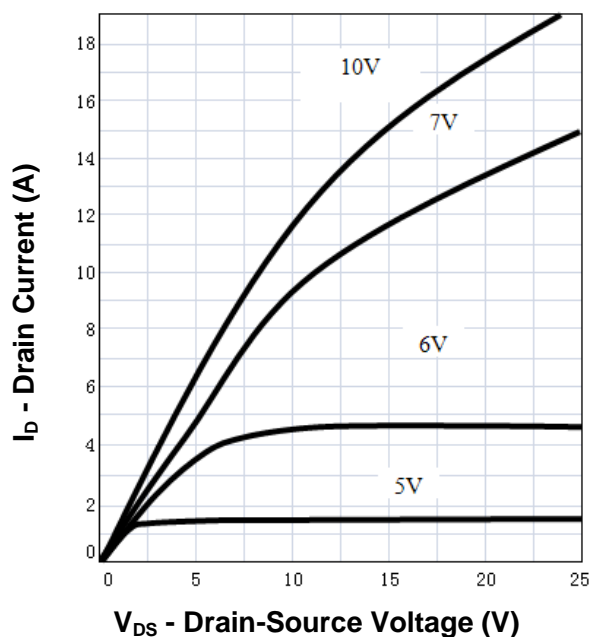
- Notes: ① Current limited by maximum junction temperature.
 ② Limited by T_{Jmax} , $I_{AS}=9.5A$, $V_{DD}=100V$, $R_G=50\Omega$, Starting $T_J=25^\circ C$.
 ③ Pulse test; Pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
 ④ Guaranteed by design, not subject to production testing.

Typical Characteristics

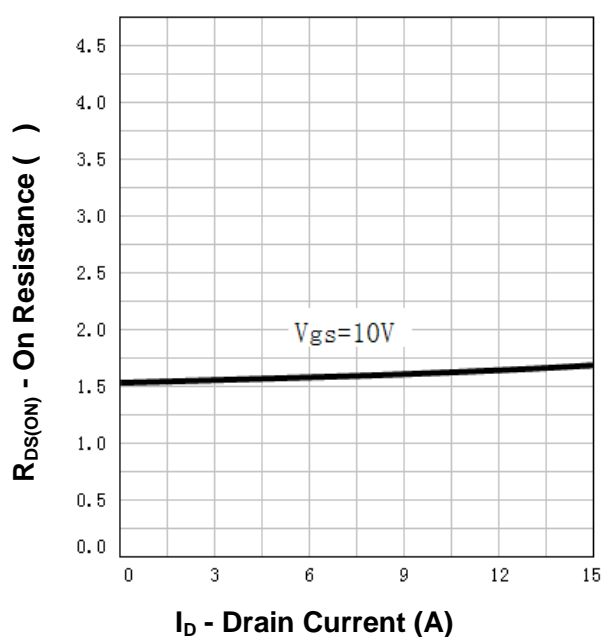


Typical Characteristics

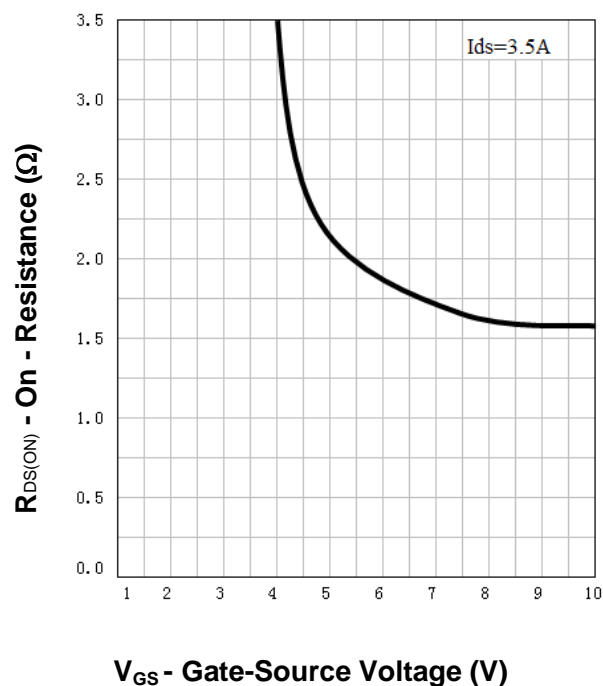
Output Characteristics



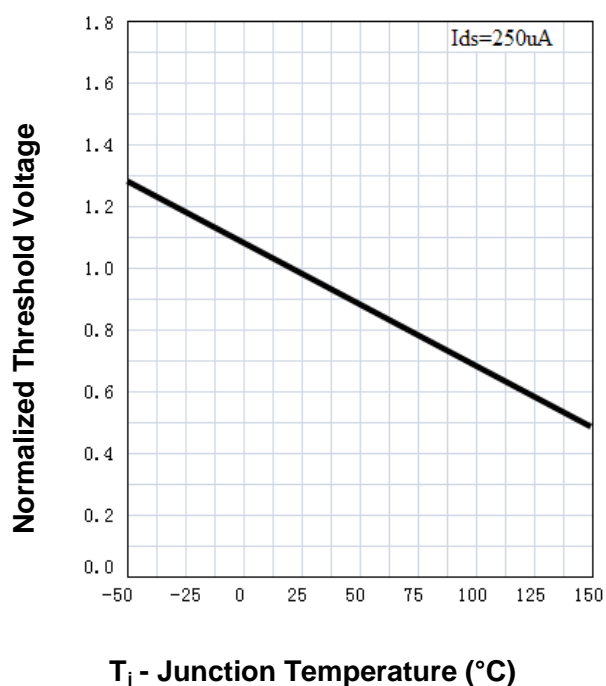
Drain-Source On Resistance



Drain-Source On Resistance

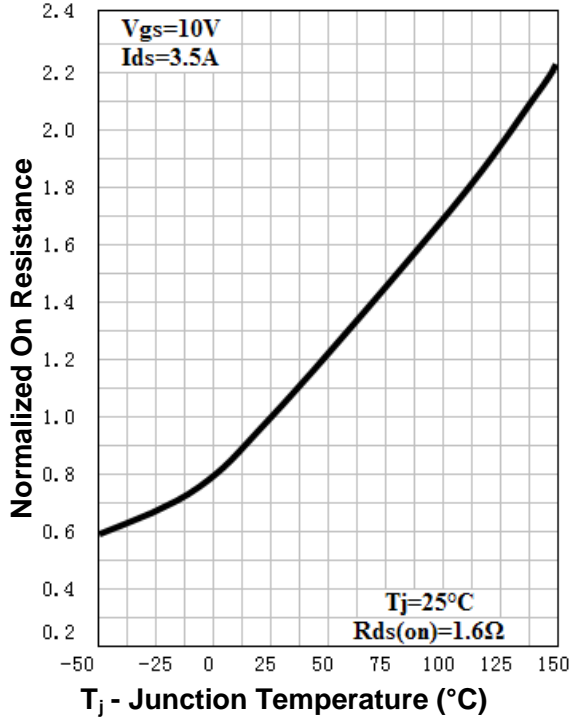


Gate Threshold Voltage

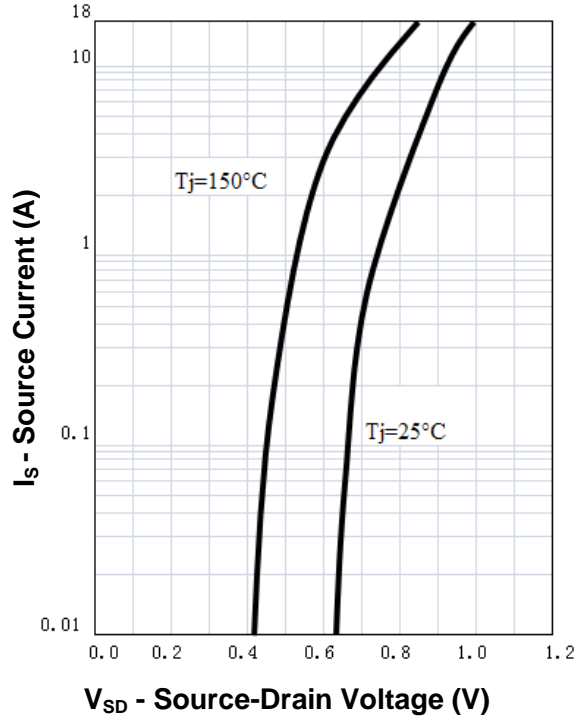


Typical Characteristics

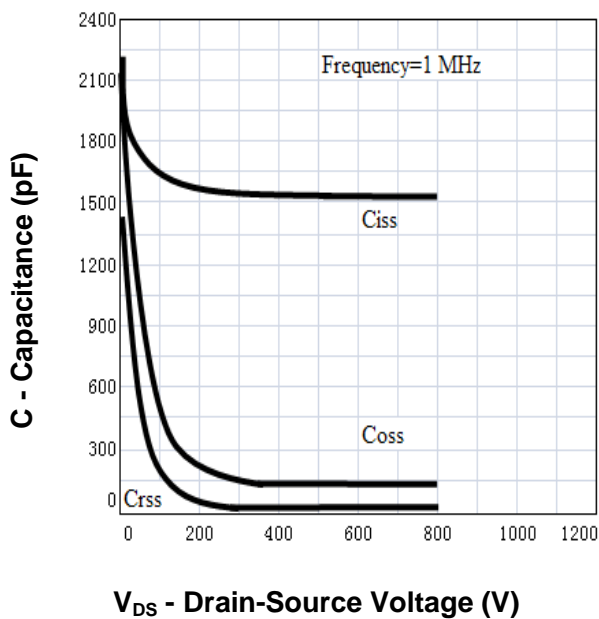
Drain-Source On Resistance



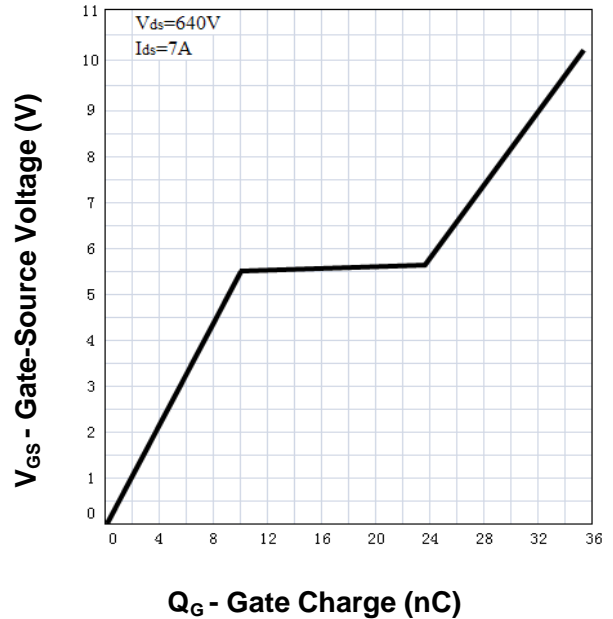
Source-Drain Diode Forward



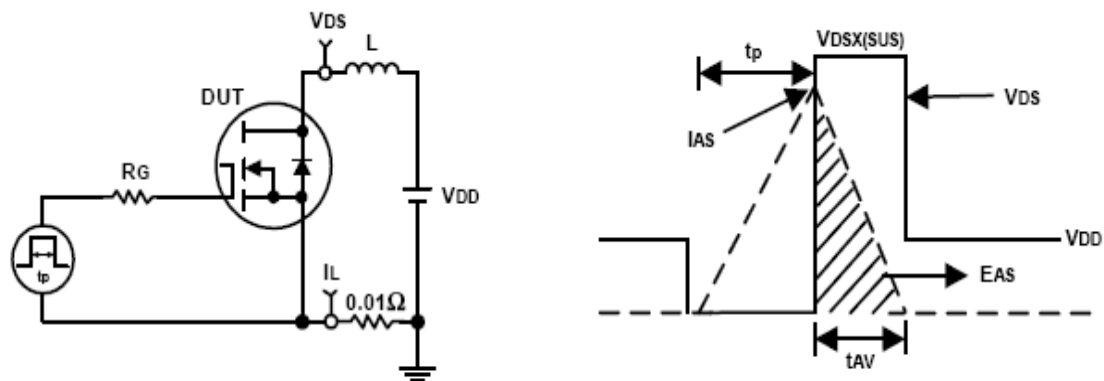
Capacitance



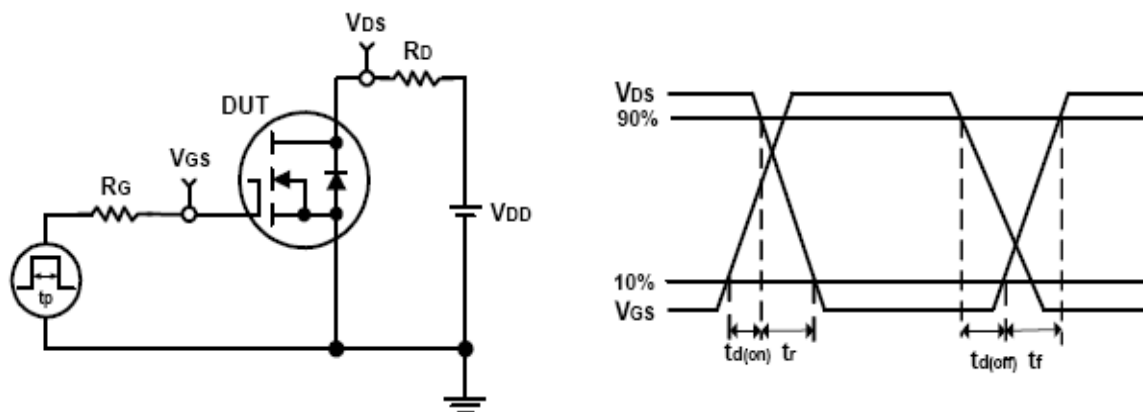
Gate Charge



Avalanche Test Circuit and Waveforms



Switching Time Test Circuit and Waveforms

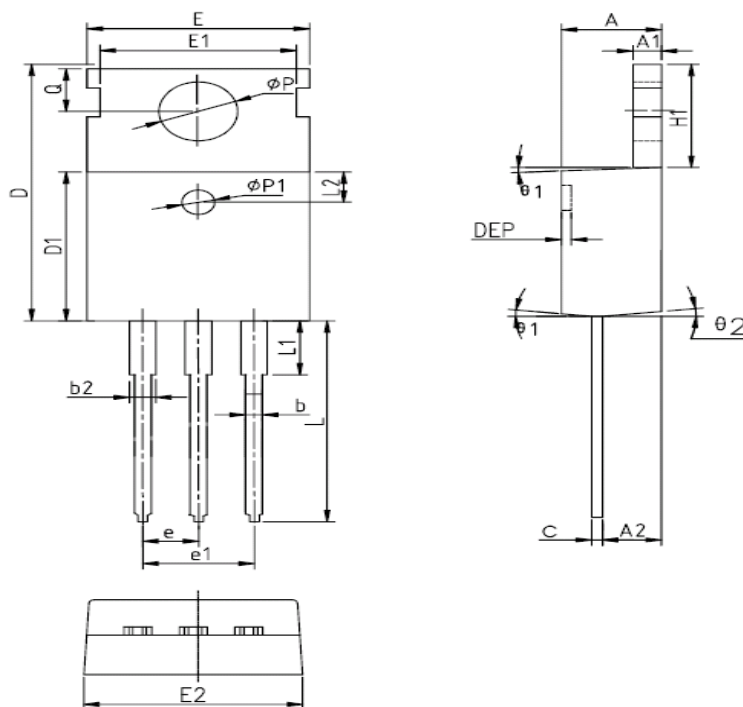


Ordering and Marking Information

Device	Marking	Package	Packaging	Quantity	Reel Size	Tape width
RU8H7R	RU8H7R	TO-220	Tube	50	-	-

Package Information

TO-220FB-3L



SYMBOL	MM			INCH			SYMBOL	MM			INCH		
	MIN	NOM	MAX	MIN	NOM	MAX		MIN	NOM	MAX	MIN	NOM	MAX
E	9.96	10.16	10.36	0.392	0.400	0.408	$\phi p3$	-	3.450	-	-	0.136	-
A	4.50	4.70	4.90	0.177	0.185	0.193	$\theta 1$	5°	7°	9°	5°	7°	9°
A1	2.34	2.54	2.74	0.092	0.100	0.108	$\theta 2$	-	45°	-	-	45°	-
A2	0.95	1.05	1.15	0.037	0.041	0.045	DEP	0.05	0.10	0.15	0.002	0.004	0.006
A3	0.42	0.52	0.62	0.017	0.020	0.024	F1	1.90	2.00	2.10	0.075	0.079	0.083
A4	2.65	2.75	2.85	0.104	0.108	0.112	F2	13.61	13.81	14.01	0.536	0.544	0.552
c	-	0.50	-	-	0.020	-	F3	3.20	3.30	3.40	0.126	0.130	0.134
D	15.67	15.87	16.07	0.617	0.625	0.633	G	3.25	3.45	3.65	0.128	0.136	0.144
Q	8.80	9.00	9.20	0.346	0.354	0.362	G1	5.90	6.00	6.10	0.232	0.236	0.240
H1	6.48	6.68	6.88	0.255	0.263	0.271	G2	6.90	7.00	7.10	0.272	0.276	0.280
e	2.54BSC			0.1BSC			b1	1.17	1.20	1.24	0.046	0.047	0.048
ϕp	-	3.183	-	-	0.125	-	b2	0.77	0.8	0.85	0.030	0.031	0.033
L	12.78	12.98	13.18	0.503	0.511	0.519	b3	1.10	1.30	1.50	0.043	0.051	0.059
D1	8.99	9.19	9.39	0.354	0.362	0.370	E1	9.8	10.00	10.20	0.386	0.394	0.412
$\phi p1$	1.40	1.50	1.60	0.055	0.059	0.063	K1	0.75	0.8	0.85	0.030	0.031	0.033
$\phi p2$	1.15	1.20	1.25	0.045	0.047	0.049							

ALL DIMENSIONS REFER TO JEDEC STANDARD
DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS

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